

# Supporting Information

## Towards efficient thick active PTB7 photovoltaic layers using diphenyl ether as a solvent additive

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**KEYWORDS:** Diphenyl ether (DPE), Solvent additive, Organic photovoltaic (OPV), Thick active layer, Low-bandgap polymer

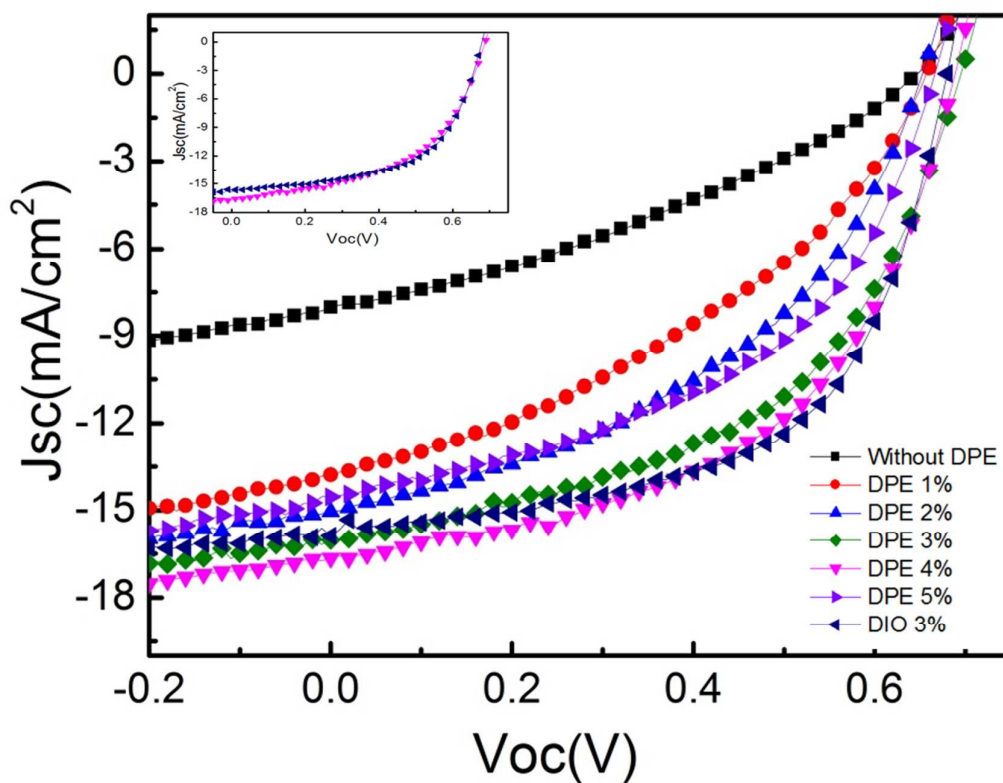
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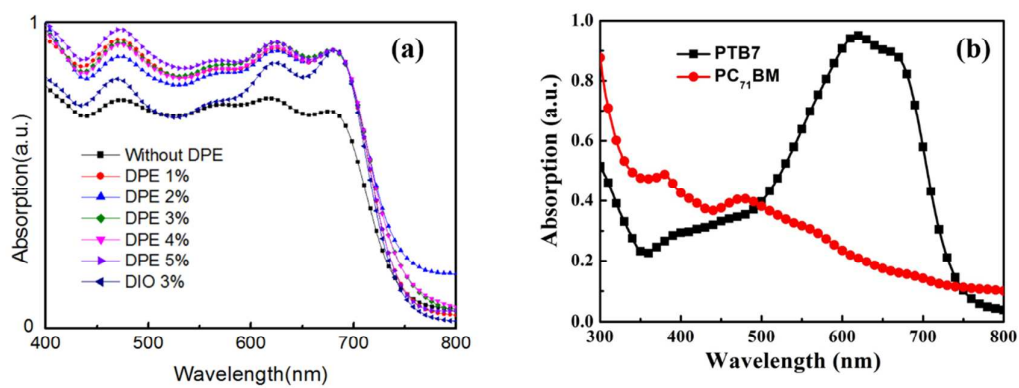
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**Table S1** Parameters employed for the fitting of the impedance spectra by use of an equivalent circuit model.

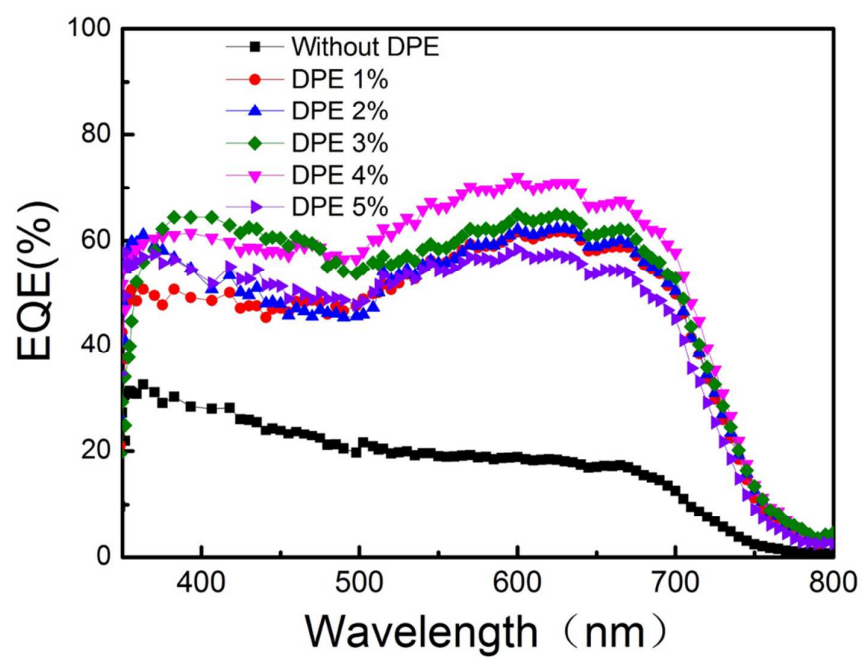
Devices	$R_1$ ( $\Omega$ )	CPE1-T (F/cm <sup>2</sup> )	CPE1-P	$R_2$ ( $\Omega$ )	$C_2$ (F)	$\tau_{avg}$ ( $\mu$ s)
Without DPE	$1.07 \times 10^3$	$4.2 \times 10^{-9}$	0.94	$1.03 \times 10^6$	$1.01 \times 10^{-9}$	4.5
DPE 2%	$6.43 \times 10^3$	$2.1 \times 10^{-9}$	0.87	$9.10 \times 10^5$	$1.17 \times 10^{-9}$	13.5
DPE 4%	$1.55 \times 10^3$	$2.4 \times 10^{-8}$	0.99	$3.00 \times 10^5$	$2.44 \times 10^{-12}$	37.1
DPE 5%	$2.77 \times 10^3$	$9.8 \times 10^{-9}$	0.98	$3.06 \times 10^5$	$3.19 \times 10^{-12}$	27.2



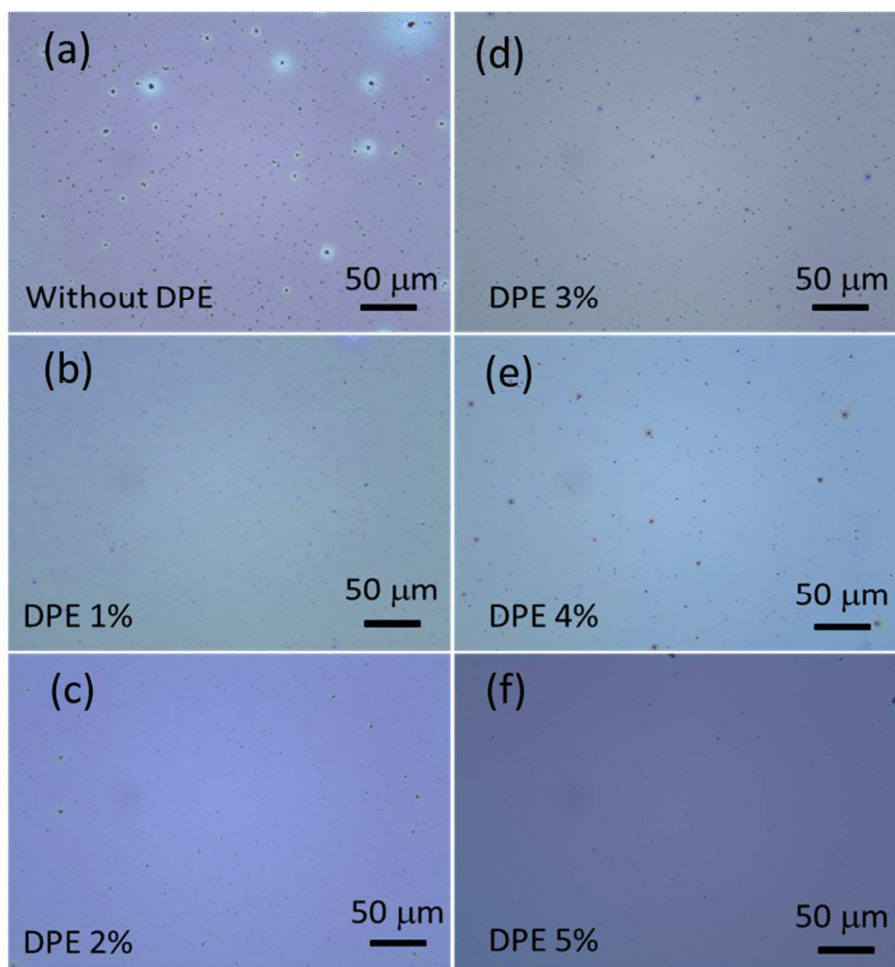
**Figure S1**  $J$ - $V$  characteristic curves of OPVs with different ratio of solvent additives; Inset: Comparison  $J$ - $V$  characteristic of the device with DIO 3% and DPE 4%.



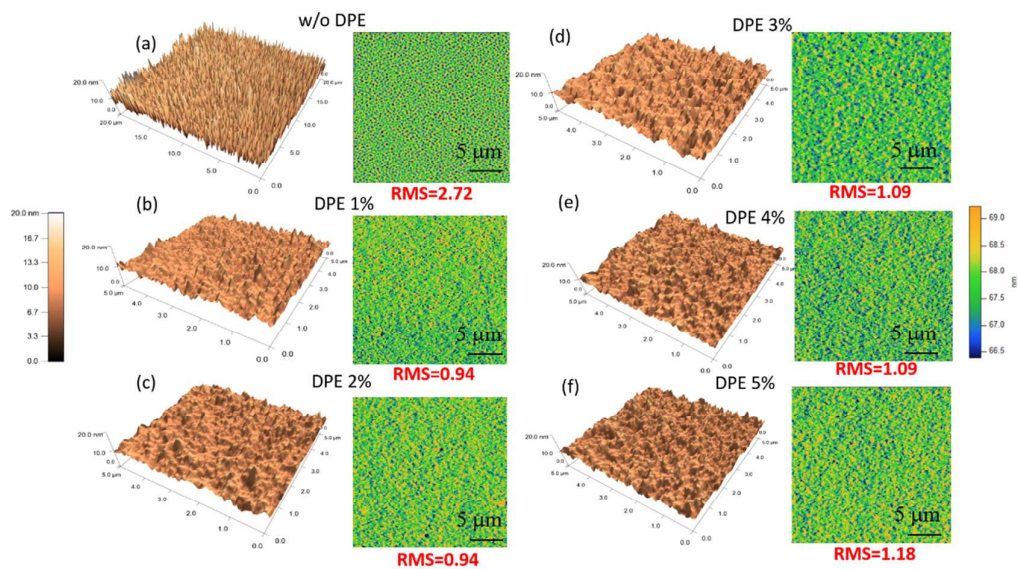
**Figure S2** UV-Vis absorption spectra of (a) the PTB7:PC<sub>71</sub>BM BHJ film with different solvent additive ratio and (b) the pure PTB7 and PCBM film.



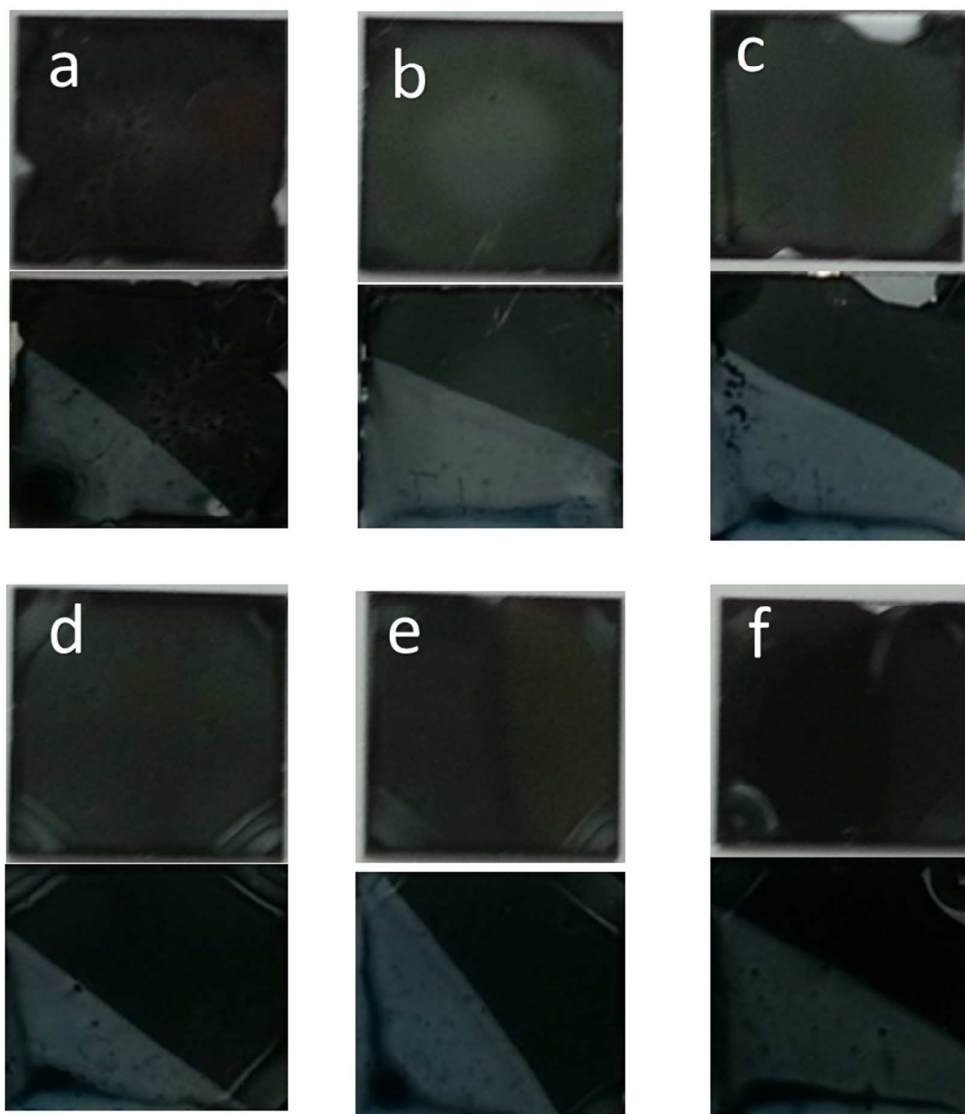
**Figure S3** External Quantum Efficiency (EQE) of device with variety ratio of DPE.



**Figure S4** Metallurgical Microscope image of PTB7:PC<sub>71</sub>BM BHJ blend film with variety concentrations of DPE, (a) without DPE, (b) DPE 1%, (c) DPE 2%, (d) DPE 3%, (e) DPE 4% and (f) DPE 5%.

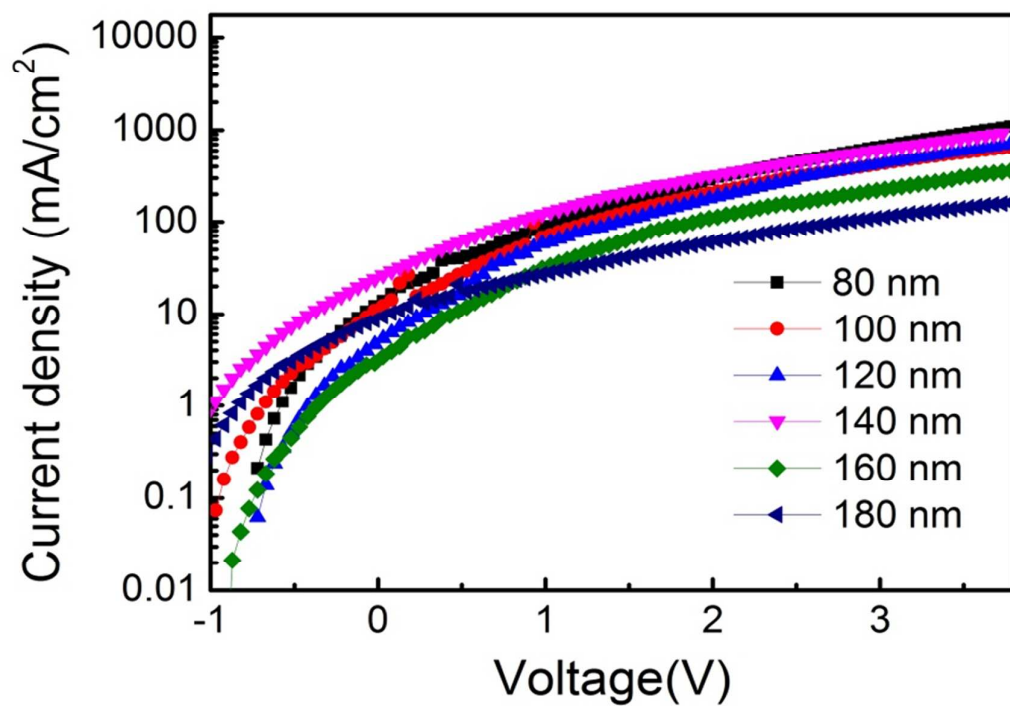


**Figure S5** AFM 3D exhibitions (left) and phase image (right) of PTB7:PC<sub>71</sub>BM BHJ blend films with different concentrations of DPE (a) without DPE, (b) DPE 1%, (c) DPE 2%, (d) DPE 3%, (e) DPE 4% and (f) DPE 5%.



**Figure S6.** Image of the PTB7:PC<sub>71</sub>BM blend film added by different concentration of DPE (up) and the film washed by CB (down). (a) without DPE, (b) DPE 1%, (c) DPE 2%, (d) DPE 3%, (e) DPE 4% and (f) DPE 5%.





**Figure S7.**  $J$ - $V$  characteristics of hole-only devices with a configuration of ITO/MoO<sub>3</sub> (15 nm)/PTB7 : PC<sub>71</sub>BM (x nm) /MoO<sub>3</sub> (15 nm)/Ag (100 nm) based on 4% DPE

### **$J_{ph}$ Calculation**

To investigate the effect of DPE on device performance, photocurrent density ( $J_{ph}$ ) of OPVs is examined.  $J_{ph}$  is defined by  $J_{ph}=J_{light} - J_{dark}$ , where  $J_{light}$  and  $J_{dark}$  represent the experimental current density measured in illumination and dark conditions, respectively.<sup>1</sup>  $J_{ph}$  can be analyzed using Equation as the analytical solution as suggested Sokel and Hughes.<sup>2</sup>

$$J_{ph} = eGL \left[ \frac{\exp(eV / kT) + 1}{\exp(eV / kT) - 1} - \frac{2kT}{eV} \right]$$

where  $e$  is the element charge,  $G$  is the charge carrier generation rate, and  $L$  is the thickness of the active layer.  $k$  is the Boltzmann constant, and  $T$  is the room temperature.  $G$  is described by a relation of  $G(T, E)=G_{max}P(T, E)$ , where  $G_{max}$  represents the total number of photogenerated charge transfer (CT), and  $P(T, E)$  is the probability for CT dissociation at the donor-acceptor interface.<sup>3</sup>

We tabulate  $J_{ph}$  of the thin PTB7:PC<sub>71</sub>BM devices with DPE additive in Table 1. OPV based on DPE 4% shows the highest  $J_{ph}$ , indicating a large number of generation of CT states as well as high CT separation efficiency.<sup>4-6</sup>

### **References**

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